First Named Inventor	Leonard Forbes
Serial No.	10/682,590
Filing Date	October 9, 2003
Group Art Unit	2811
Examiner Name	Unknown
Confirmation No.	1986
Attorney Docket No.	400.257US01

GENERAL TRANSMITTAL FORM UNDER 37 CFR 1.8
(LARGE ENTITY)

Title: FULLY DEPLETED SILICON-ON-INSULATOR CMOS LOGIC

Mail Stop Amendment
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

Enclosures

The following documents are enclosed:

X Information Disclosure Statement (1 pg.); Form 1449 (7 pgs.); 58 copies of cited references; U.S. reference(s) not included pursuant to 37 C.F.R. 1.98 (c)(2)(i);

X An itemized return-receipt postcard

Leffert Jay & Polglaze, P.A.
P.O. Box 581009
Minneapolis, MN 55458-1009
T – 612/312-2200
F – 612/312-2250

Please charge any additional fees or credit any overpayments to Deposit Account No. 501373.

CUSTOMER NO. 27073

Submitted By

Name	Kenneth W. Bolvin	Reg. No.	34,125	Telephone	(612) 312-2211
Signature	Kenneth W. Bolvin			Date	5/24/04

Certificate of Mailing

I certify that this correspondence and the identified documents listed on this transmittal are being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450 on May 24, 2004.

Name	Rhonda L. Foley	Signature	Rhonda L. Foley

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INFORMATION DISCLOSURE STATEMENT

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In compliance with 37 C.F.R. §§ 1.56 and 1.97, *et seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified Application. Pursuant to 37 C.F.R. 1.98 (a)(2)(i), as this application was filed after June 30, 2003, Applicant has not included copies of U.S. Patents or U.S. Patent Applications. Applicant respectfully requests that this Information Disclosure Statement be entered and the references listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to MPEP §609, Applicant further requests that the Examiner initial next to each reference on the Form 1449 to indicate that the listed references have been considered. Applicant further requests that a copy of the initialed Form 1449 be returned with the next official communication.

As an Office Action has not yet issued in this application, Applicant believes that no fees are due. However, the Commissioner for Patents is hereby authorized to charge any additional fees to Deposit Account No. 501373. If the Examiner has any questions or concerns regarding this application, please contact the undersigned at (612) 312-2211.

Respectfully submitted,

Date: 5/24/04

Kenneth W. Bolvin
Reg. No. 34,125

Attorneys for Applicant
Leffert Jay & Polglaze
P.O. Box 581009
Minneapolis, MN 55458-1009

T 612 312-2200
F 612 312-2250

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Title: FULLY DEPLETED SILICON-ON-INSULATOR CMOS LOGIC

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